NSN 5962-01-181-3107

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View Online at https://aerobasegroup.com/nsn/5962-01-181-3107

Body Length:
1.060 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
0.185 inches
Maximum Power Dissipation Rating:
2.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and monolithic and bipolar
Inclosure Material:
Ceramic and glass
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Bipolar metal-oxide semiconductor
Input Circuit Pattern:
12 input
Case Outline Source And Designator:
D-8 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes reverse current, dc
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
5.0 volts power source
Time Rating Per Chacteristic:
45.00 nanoseconds propagation delay time, low to high level output and 45.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Pal
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

20 printed circuit

Specification Data:

81349-mil-m-38510/503 government specification

Shelf Life:

NI/o

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Unit Of Measure:

Demilitarization:

No

Fiig:

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